TOSHIBA Infrared LED GaAłAs Infrared Emitter

# TLN227(F)

#### Lead(Pb)-Free

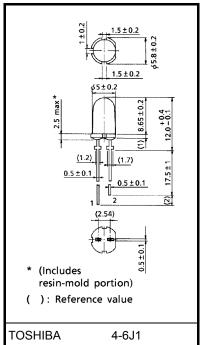
#### For Space-Optical-Transmission

- High radiant power: Po = 18mW (typ.) at IF = 50mA
- Wide half-angle value: =  $\theta 1 / 2 \pm 21^{\circ}$  (typ.)
- High-speed response: t<sub>r</sub>, t<sub>f</sub> = 30ns (typ.)
- Light source for remote control
- Designed for transmission of wireless AVsignals purpose.
- Designed for high-speed data transmission

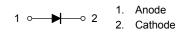
## Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Forward current	١ <sub>F</sub>	100	mA	
Pulse forward current	I <sub>FP</sub>	1000 (Note 1)	mA	
Power dissipation	PD	220	mW	
Reverse voltage	V <sub>R</sub>	4	V	
Operating temperature	T <sub>opr</sub>	-25~85	°C	
Storage temperature	T <sub>stg</sub>	-30~100	°C	
Soldering temperature (5s)	T <sub>sol</sub>	260	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



#### **Pin Connection**



Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Frequency = 100kHz, duty = 1%

#### Optical And Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Forward voltage	VF	I <sub>F</sub> = 100mA	—	1.8	2.2	V
Reverse current	۱ <sub>R</sub>	V <sub>R</sub> = 4V	-	_	60	μA
Radiant power	PO	I <sub>F</sub> = 50mA	14	18	_	mW
Radiant intensity	ΙE	I <sub>F</sub> = 50mA	-	100	_	mW / sr
Rise time, fall time	t <sub>r</sub> , t <sub>f</sub>	I <sub>FP</sub> = 100mA, P <sub>W</sub> = 100ns	-	30	_	ns
Cut-off frequency (Note 2	) f <sub>C</sub>	I <sub>F</sub> = 50mA <sub>DC</sub> + 5mAp–p	10	15	_	MHz
Capacitance	CT	V <sub>R</sub> = 0, f = 1MHz	-	110	_	pF
Peak emission wavelength	λP	I <sub>F</sub> = 50mA	830	870	900	nm
Spectral line half width	Δλ	I <sub>F</sub> = 50mA	_	50	_	nm
Half value angle	$\theta \frac{1}{2}$	I <sub>F</sub> = 50mA	_	±5	—	0

Note 2: Frequency when modulation light power decreases by 3dB from 1 MHz.

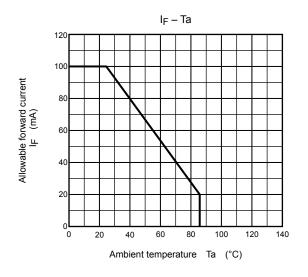
Unit: mm

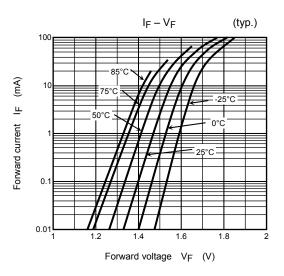
## Precautions

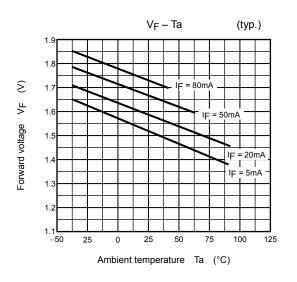
Please be careful of the followings.

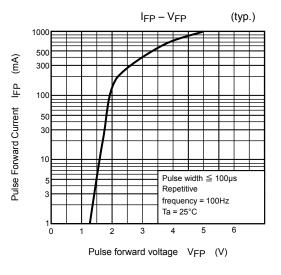
- 1. Soldering must be performed under the lead stopper.
- 2. When forming the leads, bend each lead under the stopper without leaving forming stress to the body of the device. Soldering must be performed after the leads have been formed.
- 3. Radiant power falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in radiant power over time.

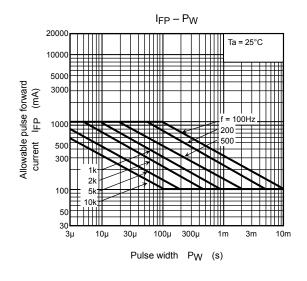
# **TOSHIBA**

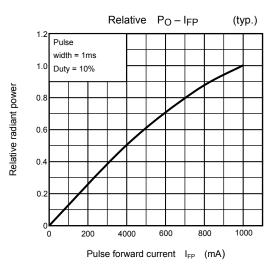




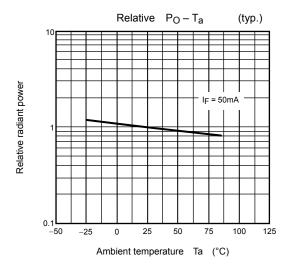


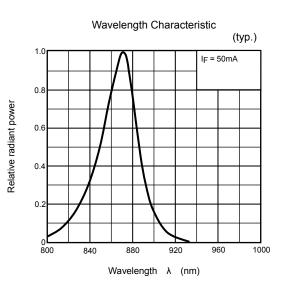


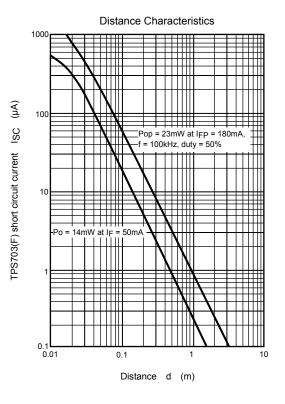


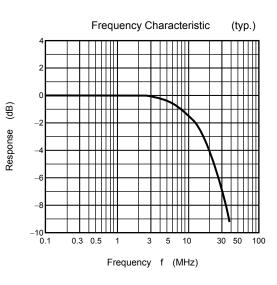


## TOSHIBA

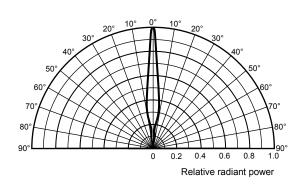








Radiation Pattern (typ.) Ta = 25°C



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